

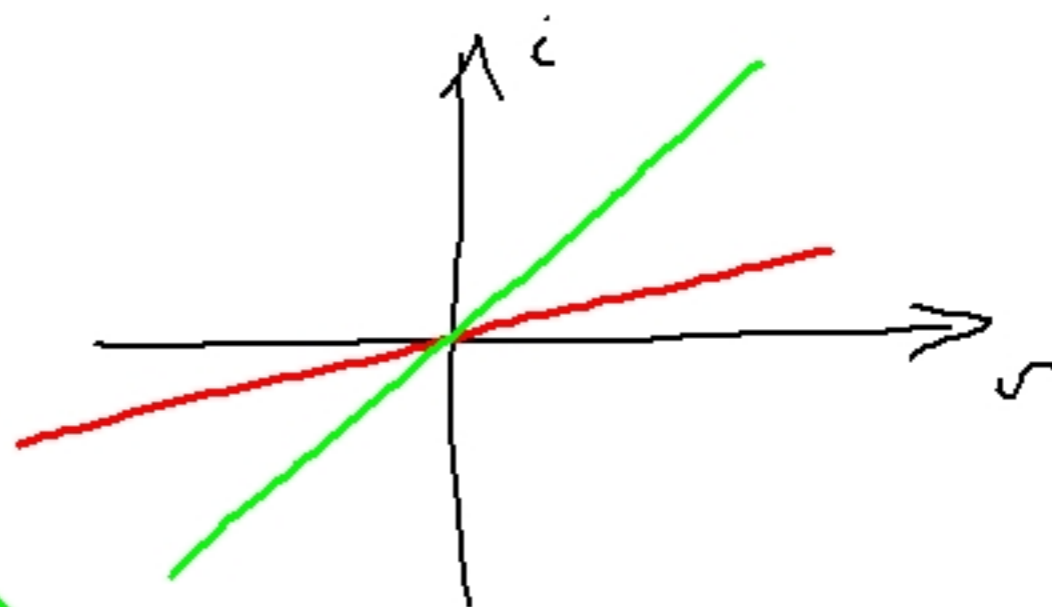
LECTURE 23 - PHOTO DETECTORS

PHOTODIODES



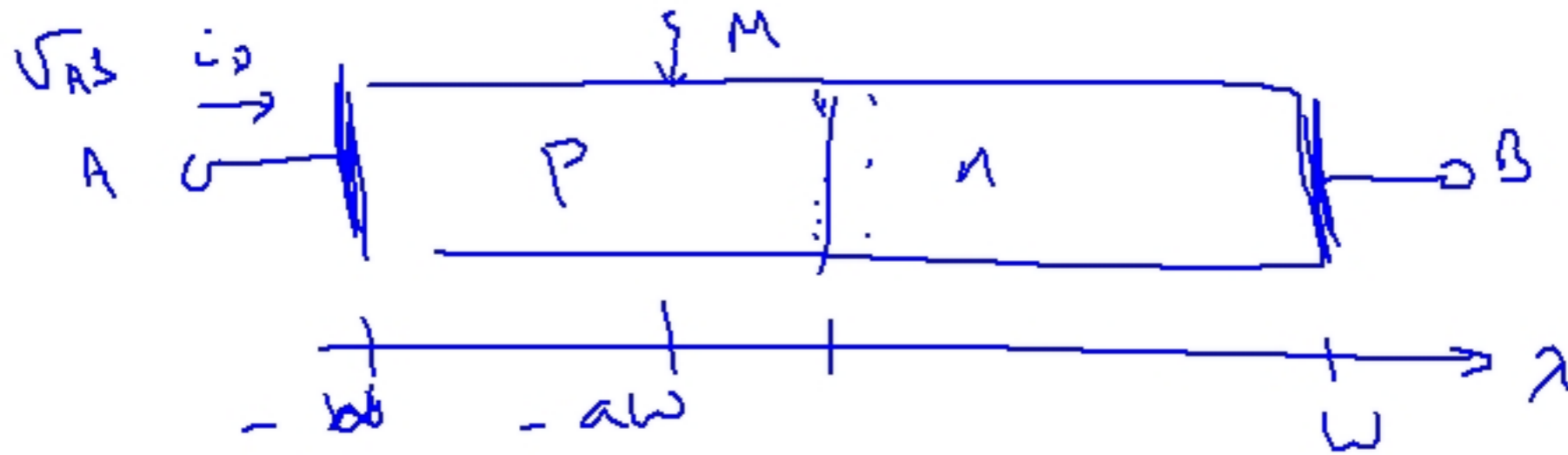
DARK
ILLUMINATED

PHOTOCONDUCTORS



PHOTODIODES

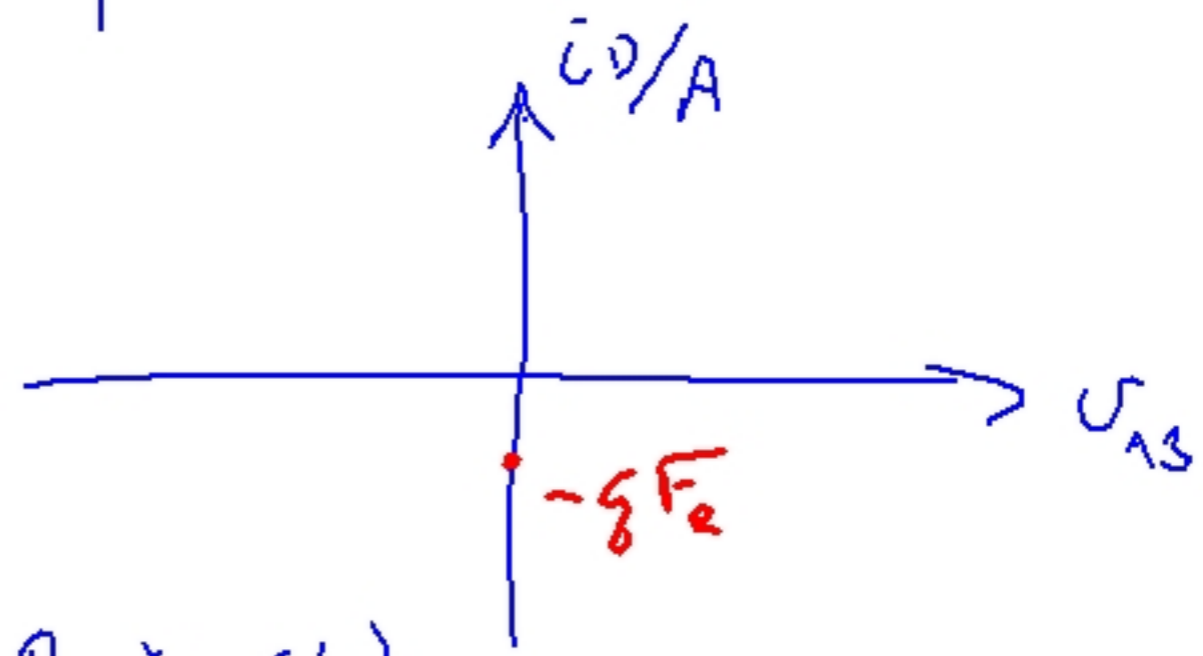
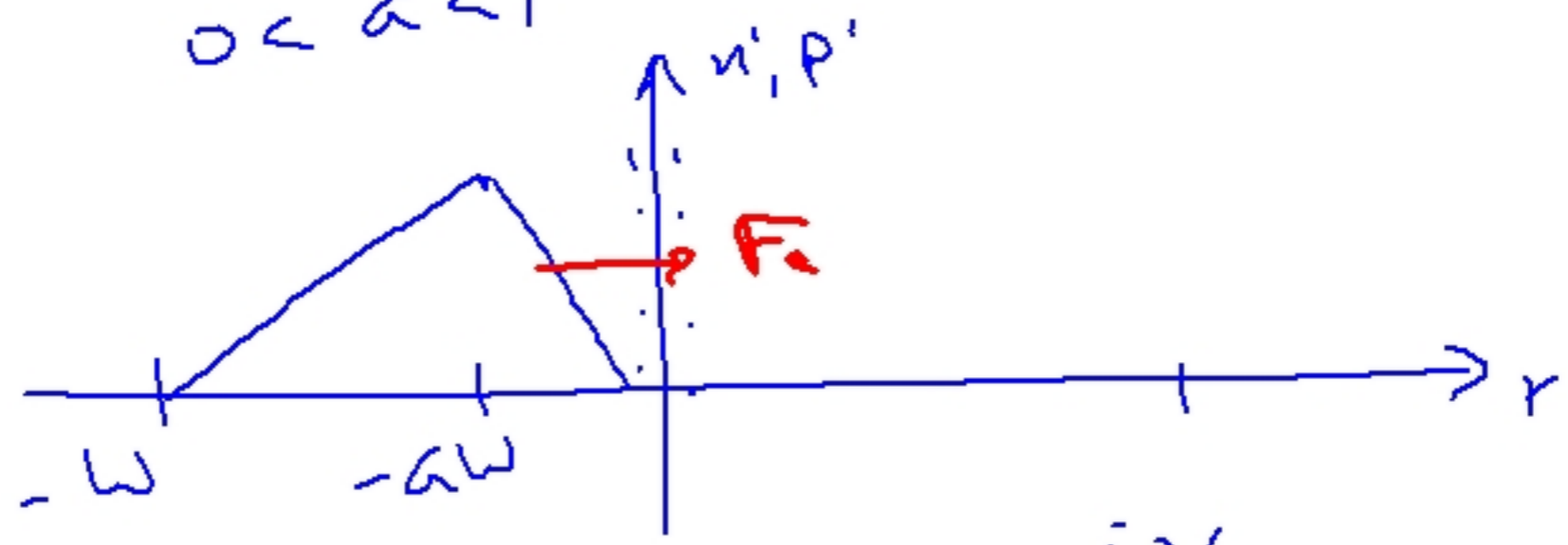




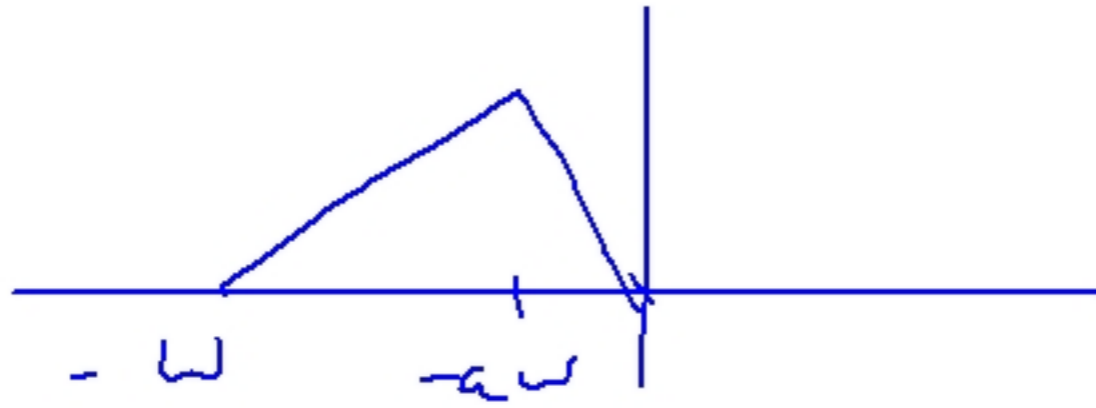
Z

$0 < a < L$

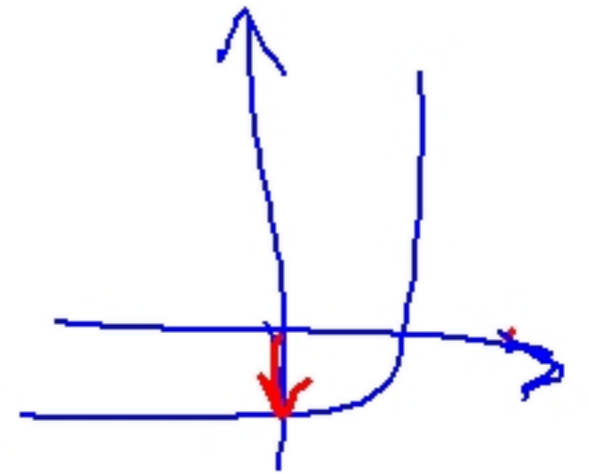
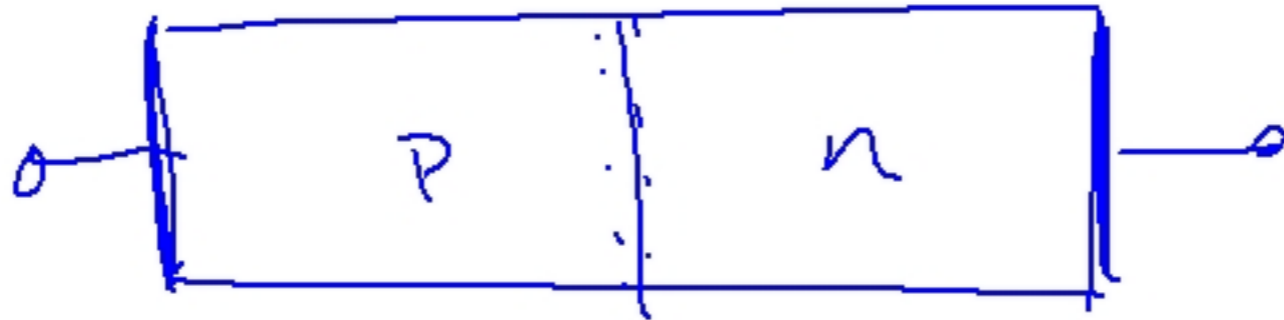
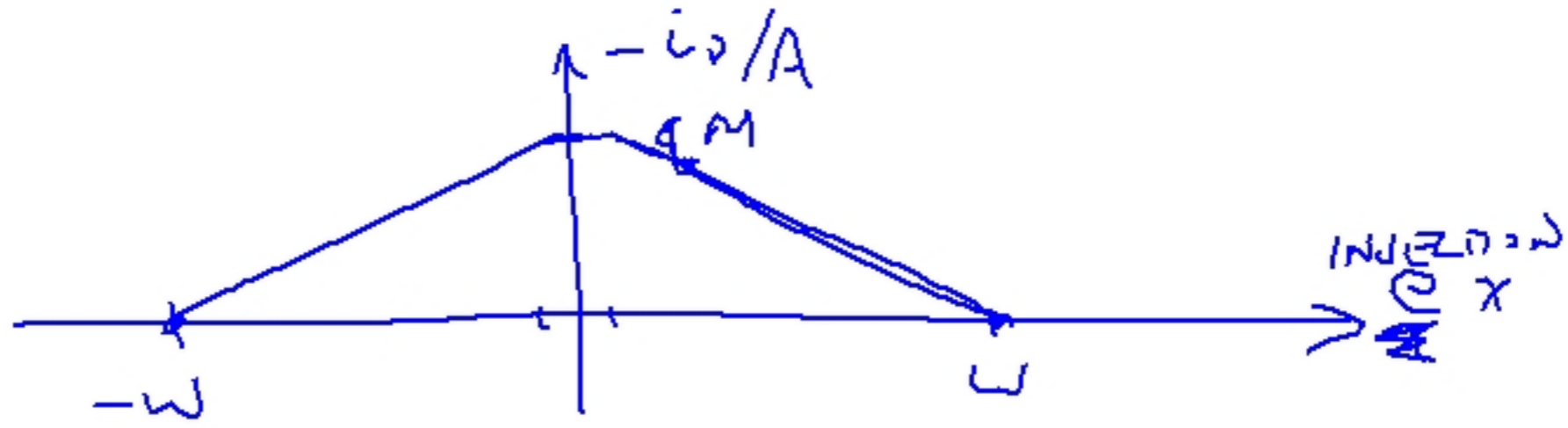
$U_{AB} = 0$



GM carries $(L)^2 @ x = a$



$$\frac{I_0}{A} = J_e = -gM(1-a)$$



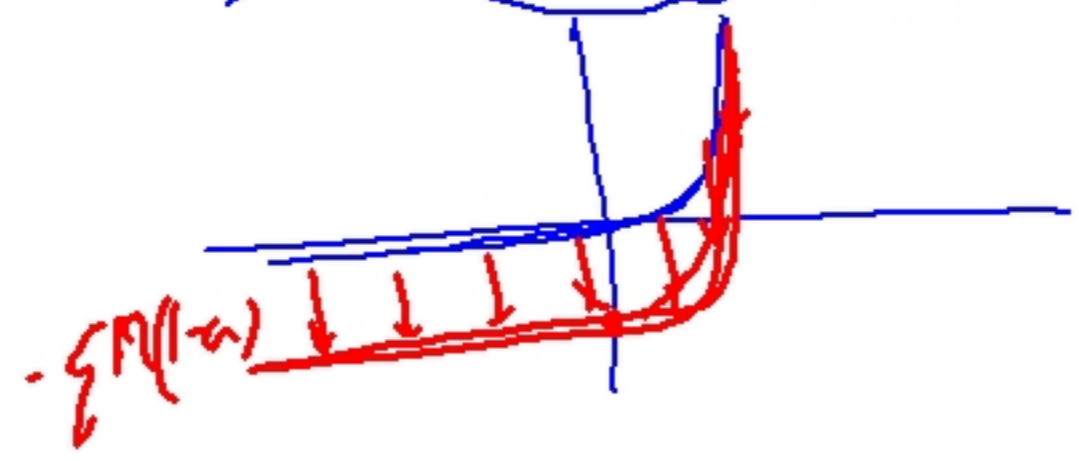
Want

$$i_D(M@a, V_{AB}) = i_D(M@a, 0) + i_D(0, V_{AB})$$

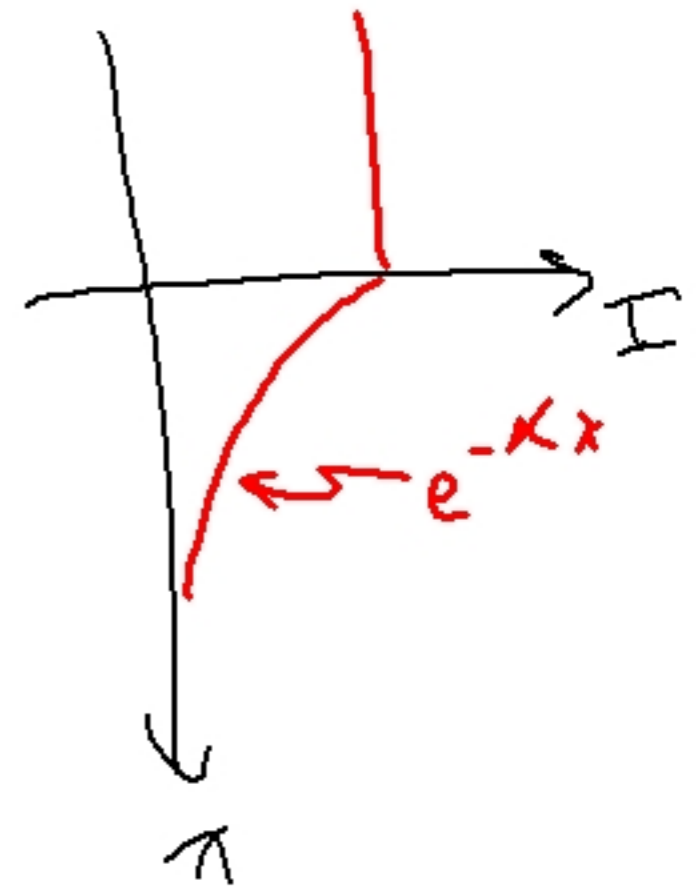
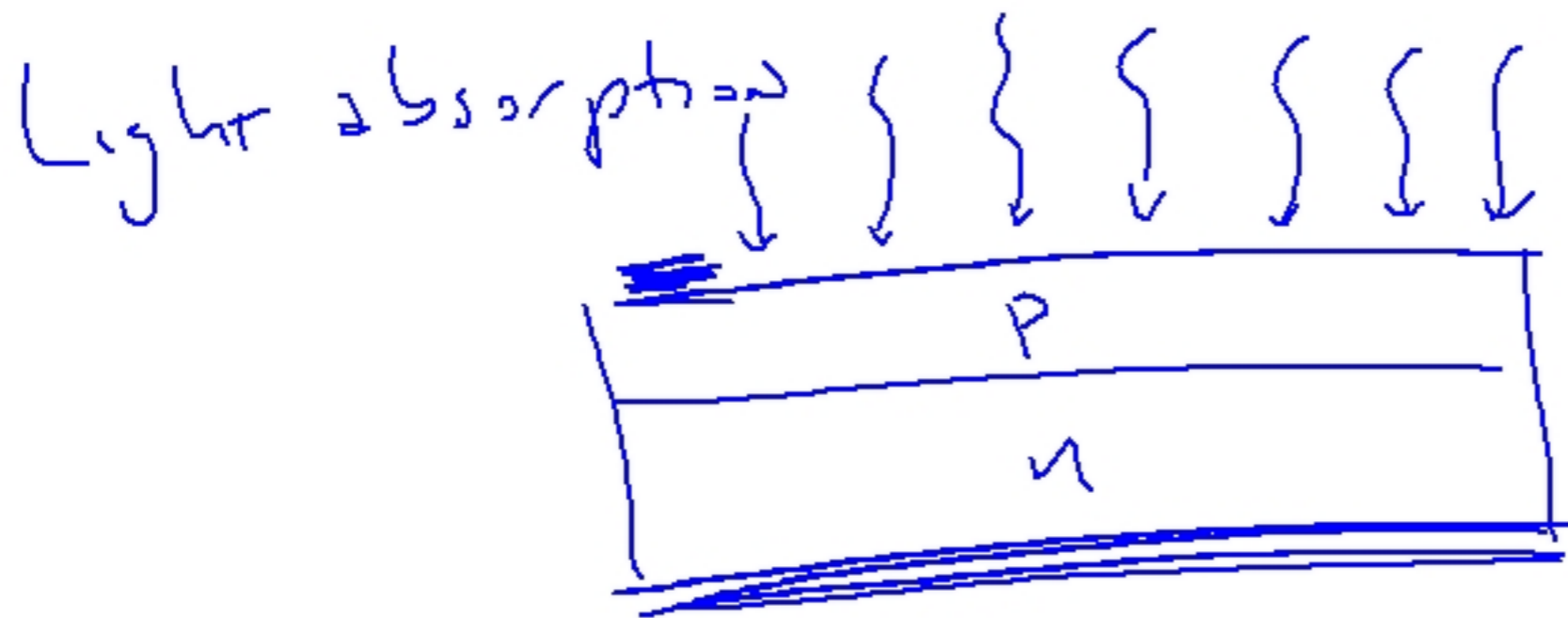
$$i_D(0, V_{AB}) = I_S (e^{qV_{AB}/kT} - 1)$$

$$i_D(M@a, 0) = -gM(1-a)$$

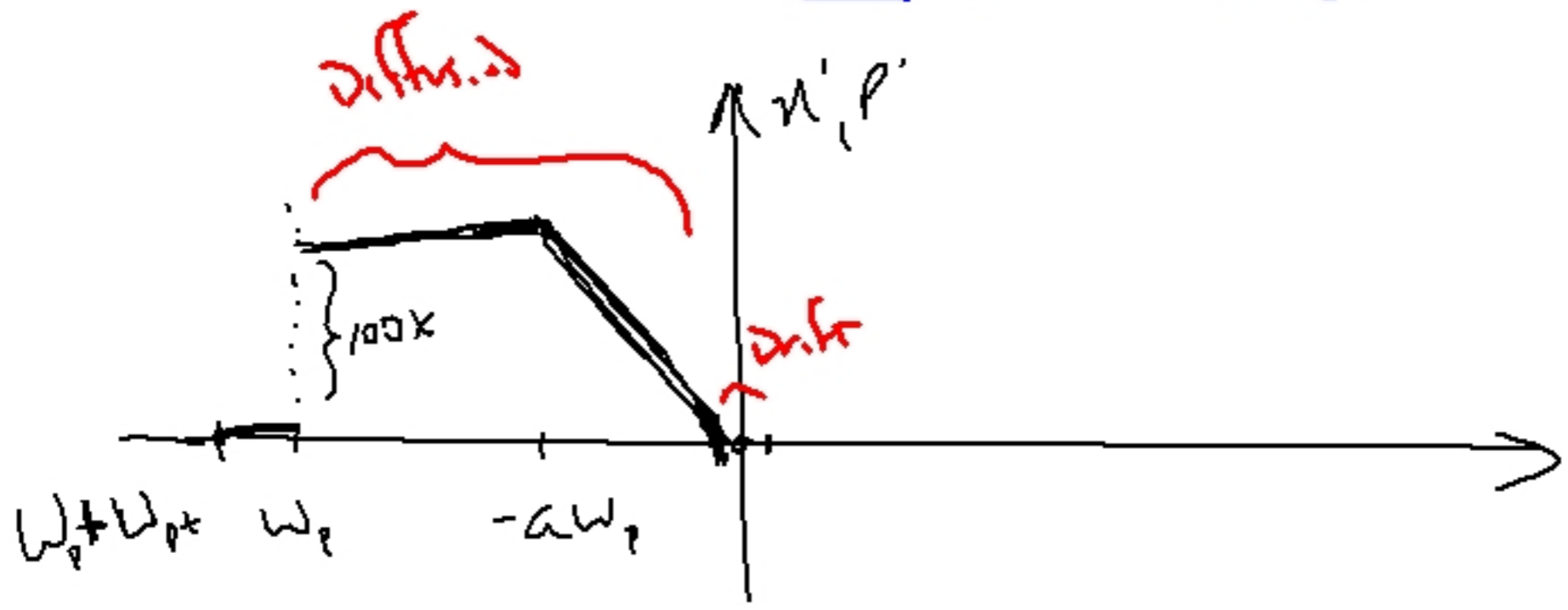
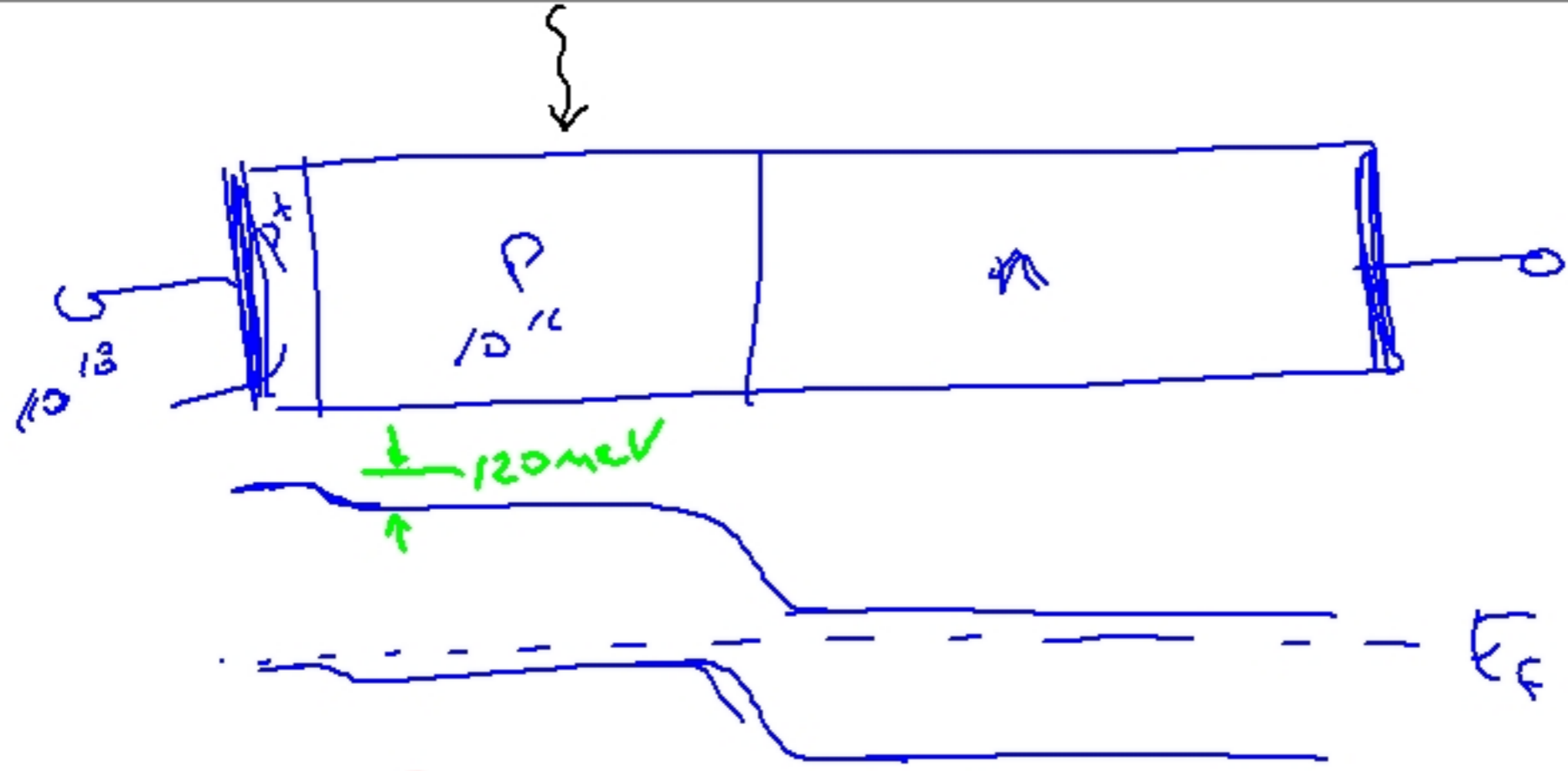
$$i_D(M@a, V_{AB}) = \underbrace{I_S (e^{qV_{AB}/kT} - 1)}_{\text{blue}} - \underbrace{gM(1-a)}_{\text{red}}$$



LESSON SO FAR - 100% eff if illuminated \int
w SCL

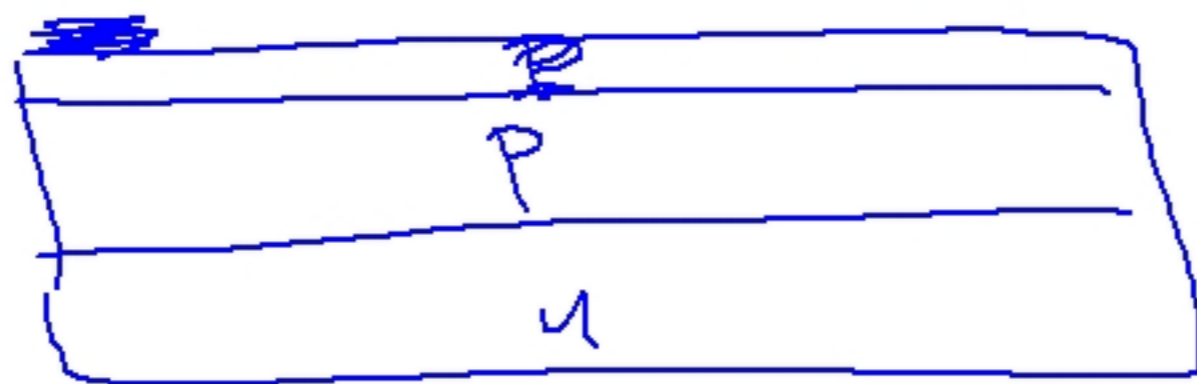
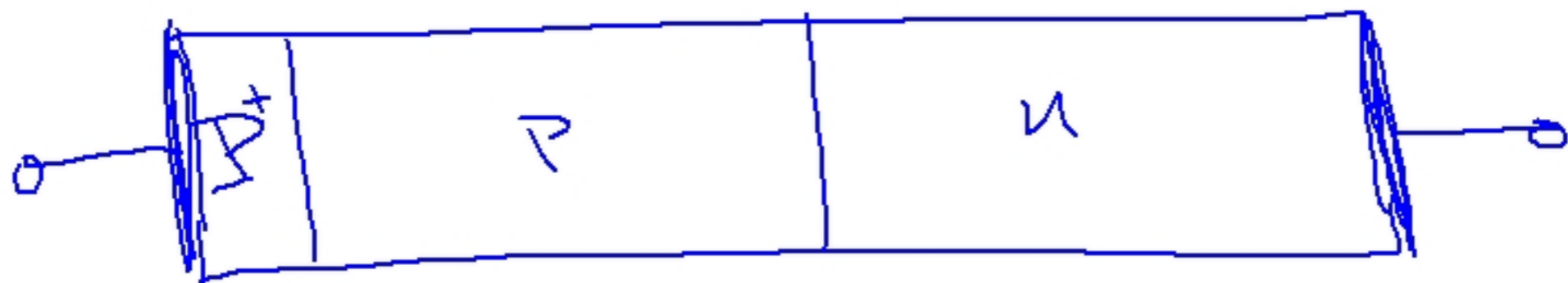


How do we get carriers generated near
SURFACE TO CROSS THE JUNCTION?

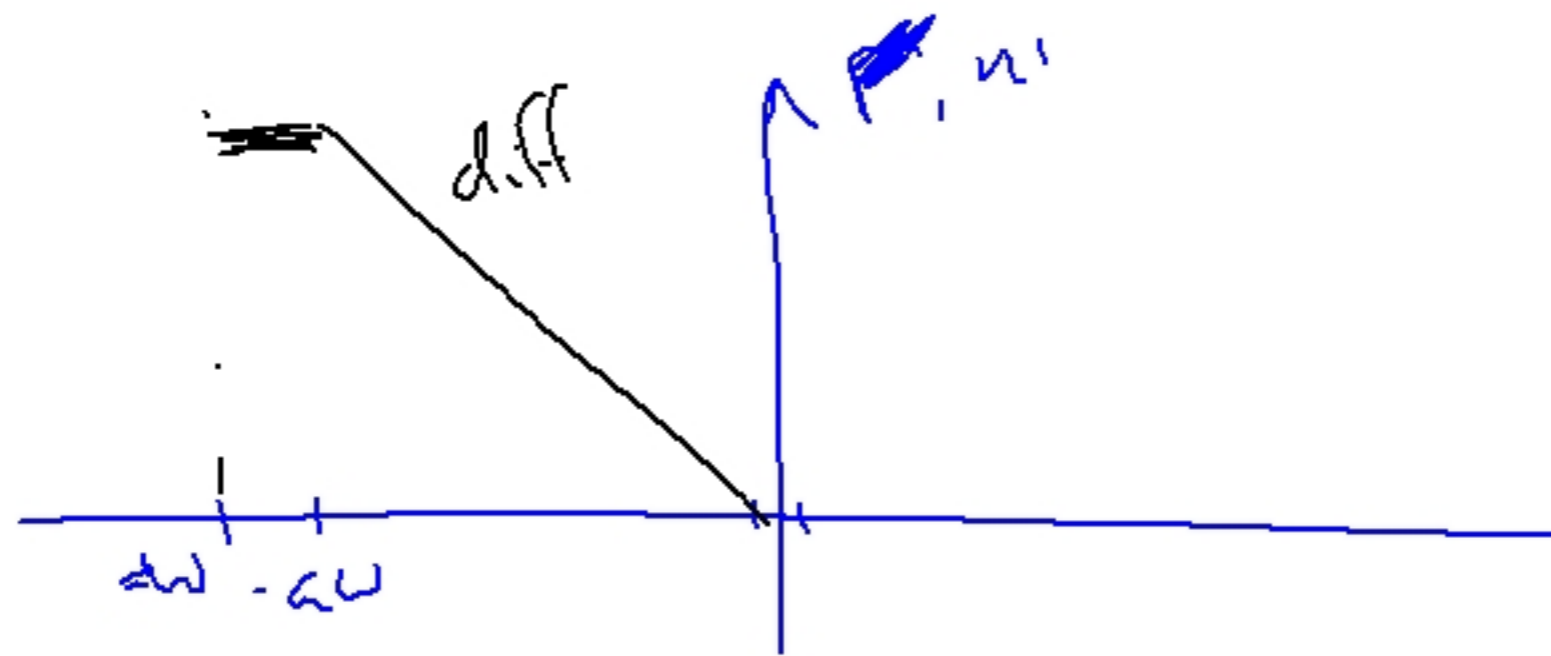


∴ SURFACE BARRIER LAYER WORKS WELL
BUT THERE IS STILL APPRECIABLE ABSORPTION
 IN THIS ~~PT~~ LAYER

Solution — WIDE BANDGAP WINDOW LAYER 7



THIS GIVES GOOD RESPONSIVITY (i.e. high η)
WHAT ABOUT SPEED?



COMPARE TRANSIT TIMES ACROSS d

$$\tau_{tr, Diff} \approx d^2 / 2D_e$$

$$\tau_{tr, Drift} \approx \frac{d}{v_{drift}} = \frac{d}{S_{set}}$$

$$\frac{\tau_{tr, Drift}}{\tau_{tr, Diff}} = \frac{2D_e}{S_{set} d} = \frac{2 \times 10^2}{10^3} = 0.2$$

$$d = 1 \mu m = 10^{-4} \text{ cm}$$

$$S_{set} = 10^7 \text{ cm/s}$$

$$D_e = 10^2 \text{ cm}^2/\text{s}$$

$$\tau_{\text{drift}} = \frac{1}{5} \tau_{\text{diff}}$$

Tells us diode would be much faster
if all light was absorbed in a
depletion region!

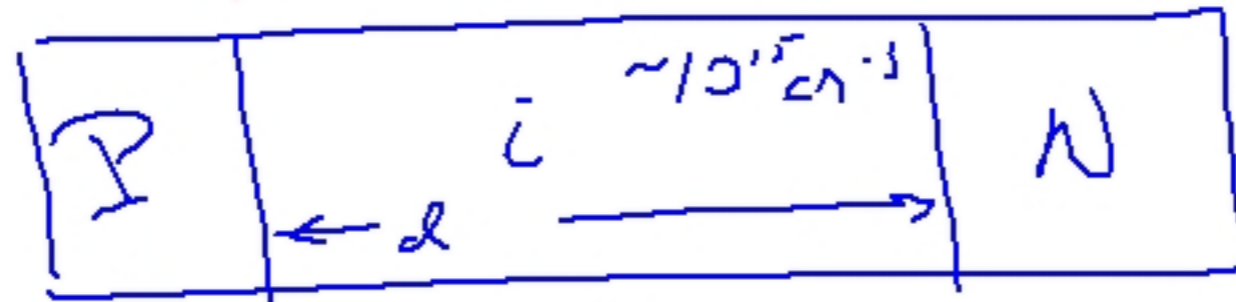
To get a depletion region that is
1-2 μm wide @ a few volts, you
need very light doping.

\Rightarrow p-i-n

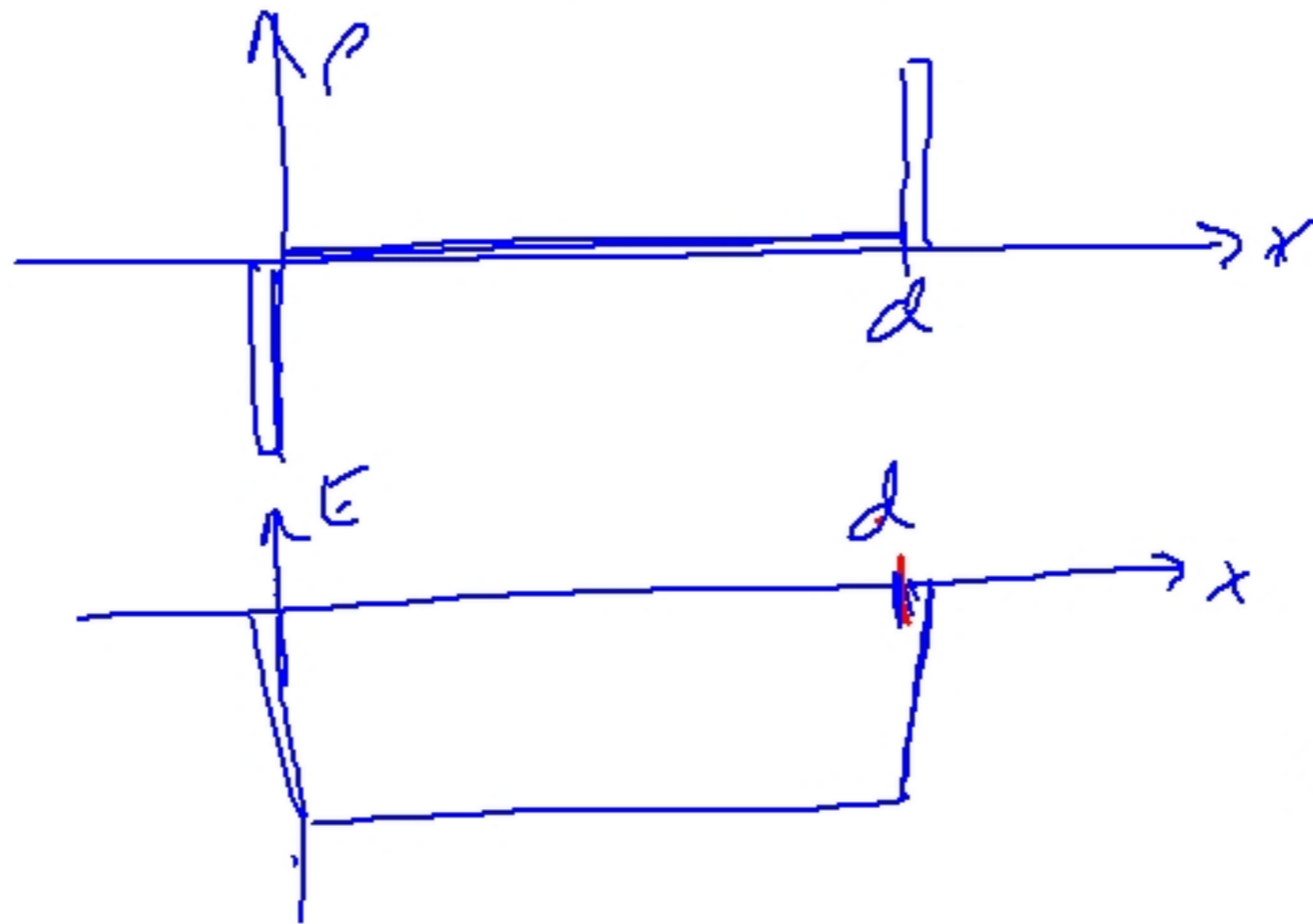
P-i-N

absorbing region
& drift region

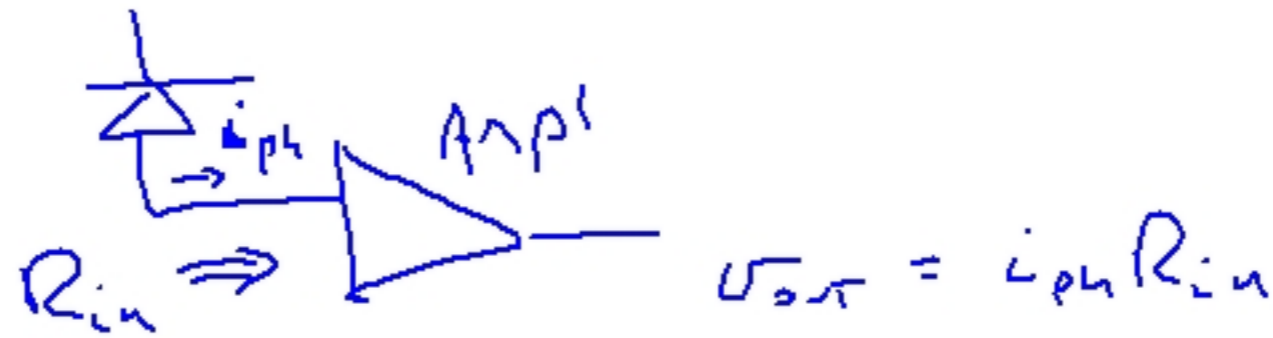
10



$d = 1-2 \mu\text{m}$ typ.



P.N SPERN



$$\tilde{Z}_{rc} = (C_{det} + \cancel{C_{in amp}}) R_{in}$$

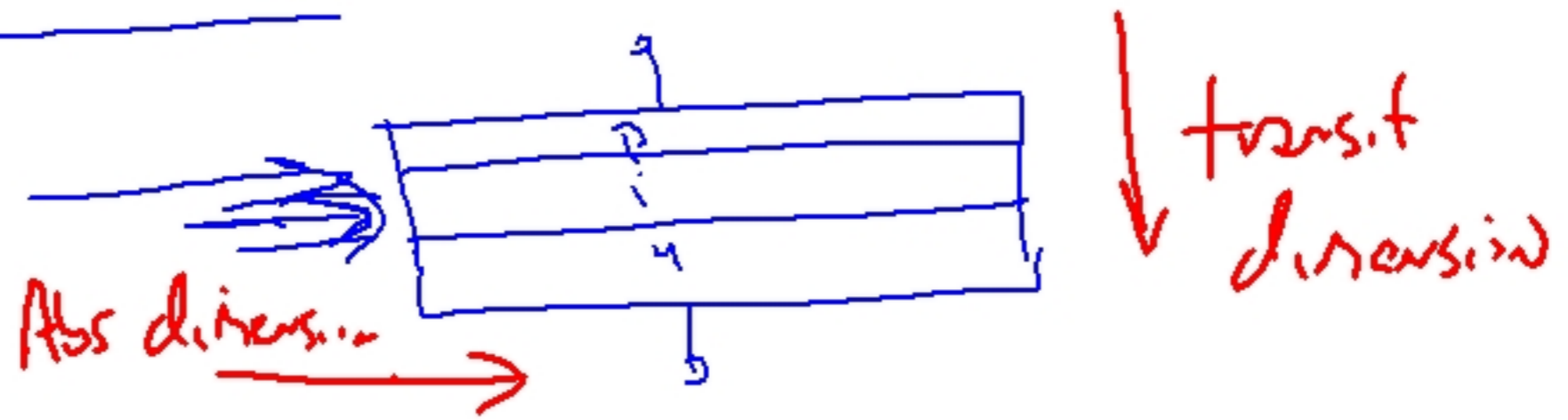
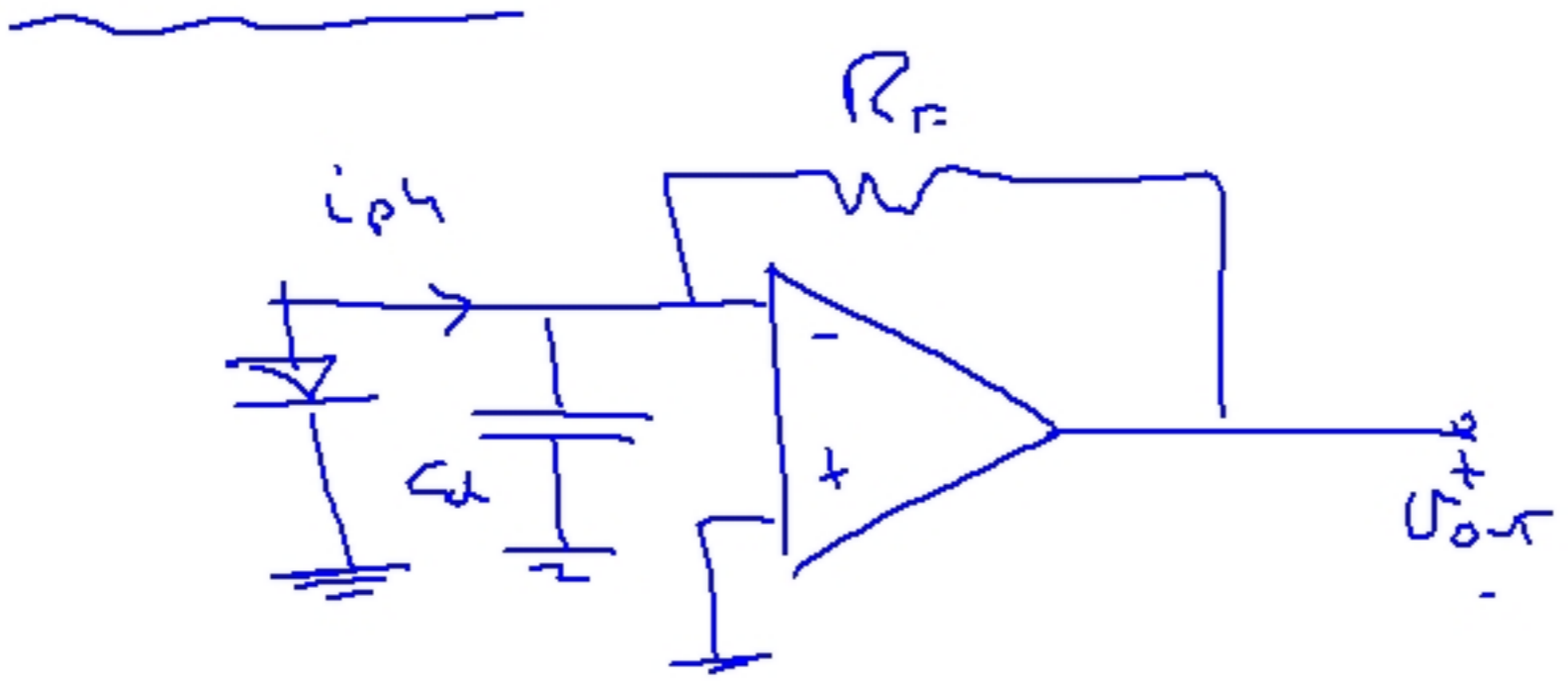
$$\approx \frac{\epsilon A}{d} R_{in}$$

$$\tilde{Z}_{tr} = \frac{d}{S_{set}}$$

$$\tilde{Z}_{TOT} = \frac{d}{S_{set}} + \frac{\epsilon A}{d} R_{in}$$

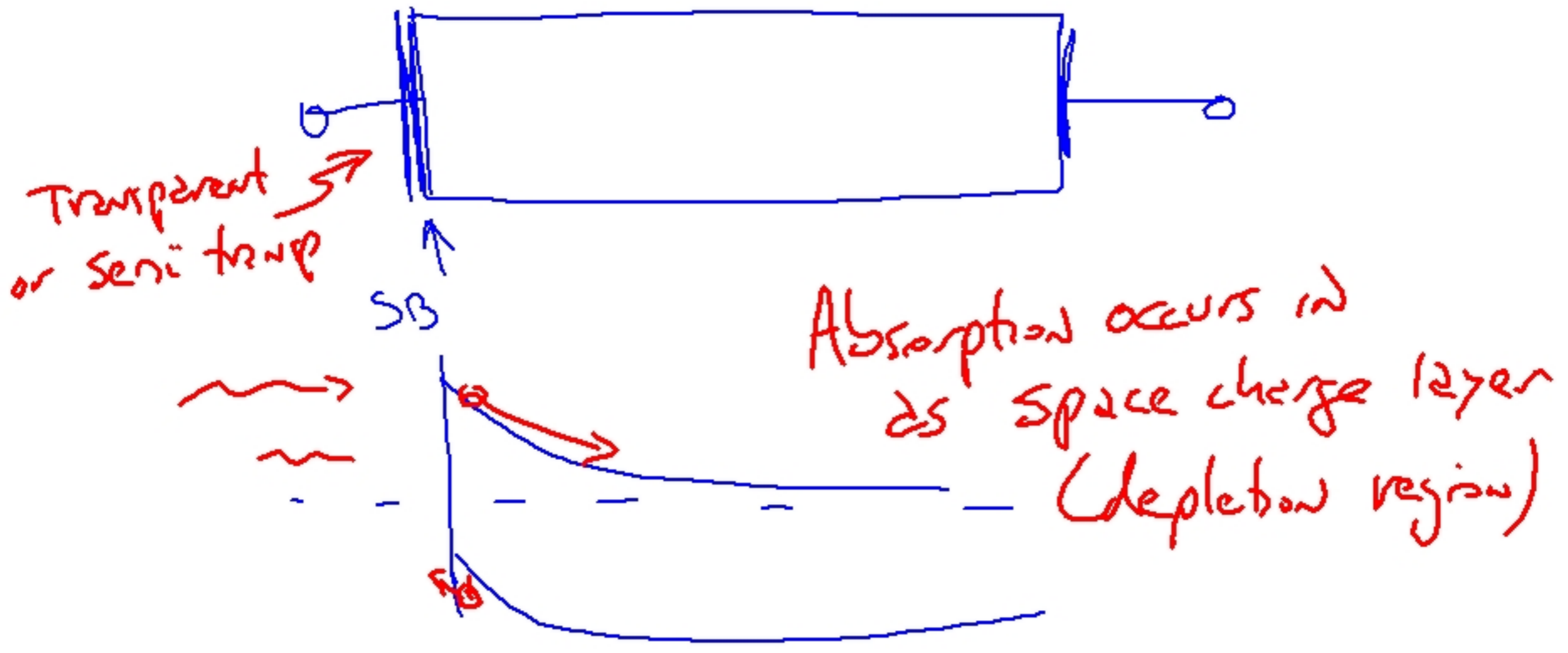
$$Z_{TOT \text{ MID}} = Z \sqrt{\frac{R_{in} A}{S_{set}}}$$

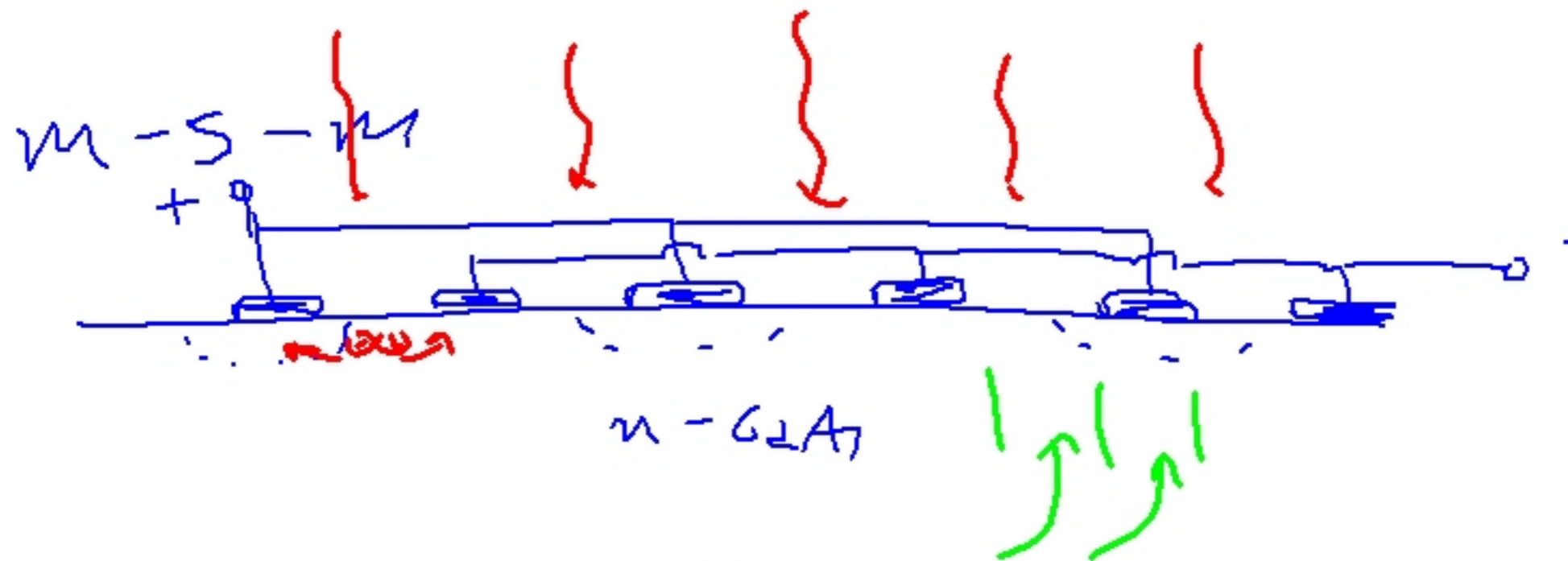
$$d_{opt} = \sqrt{S_{set} R_{in} A}$$



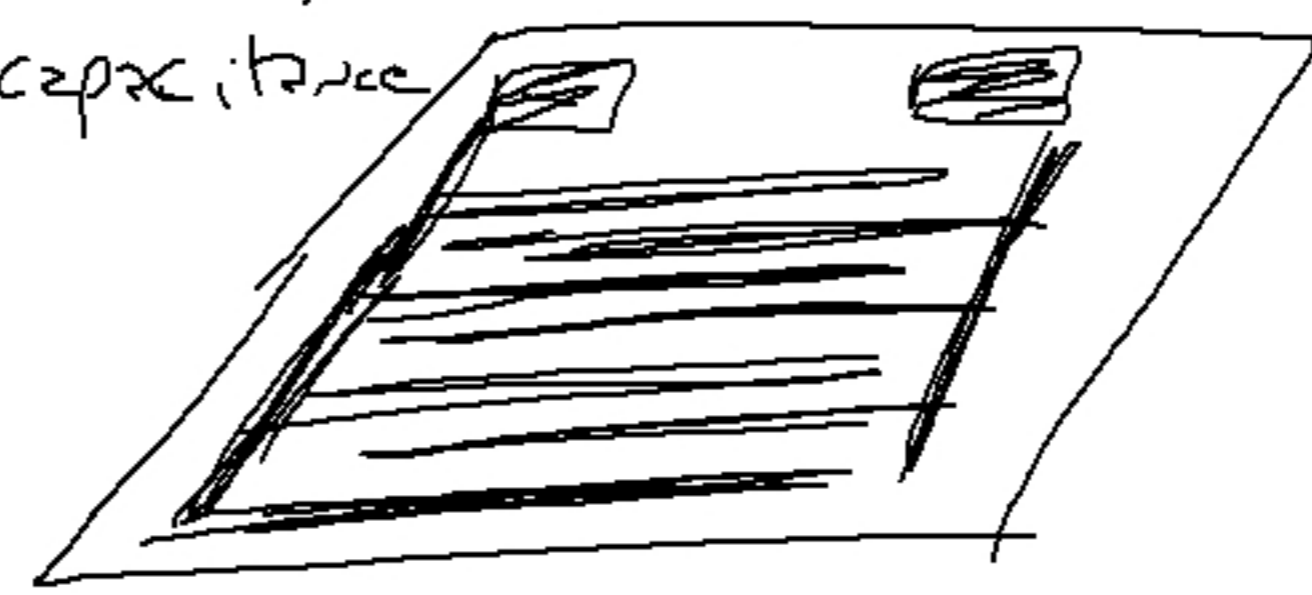
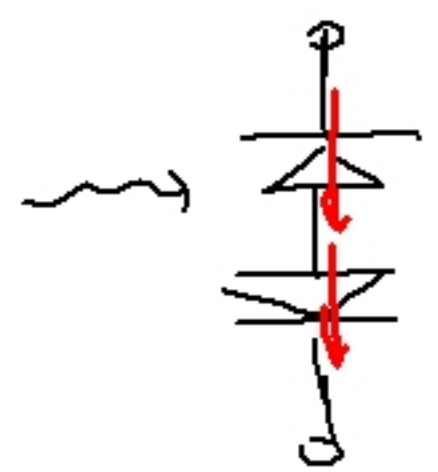
P-n diode
P-i-n diode

Metal-semiconductor diode
(Schottky barrier)





Distances can be very small \Rightarrow very fast
 Very low capacitance

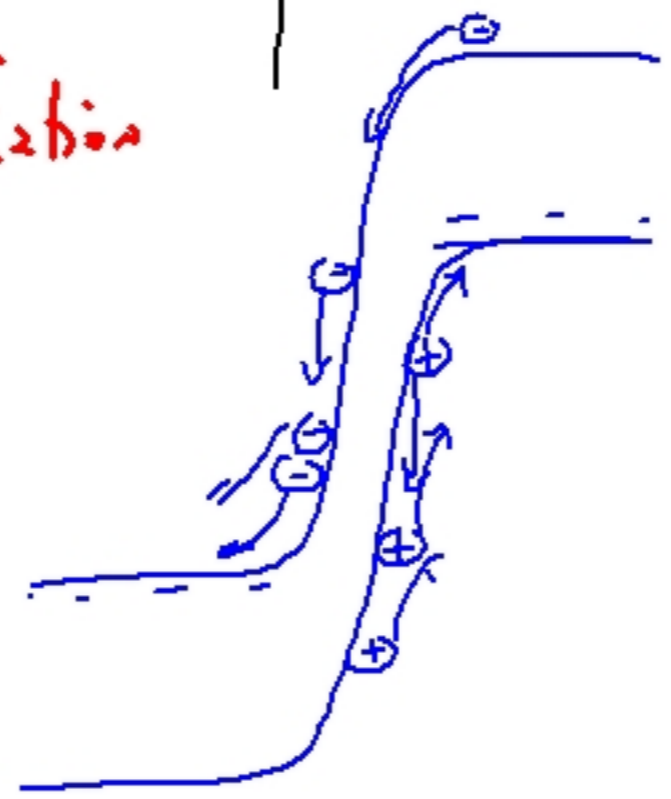


FINAN PHOTO DIODE

AVALANCHE PHOTO DIODES



Avalanche multiplication



A photodiode with gain

$$I_{ph} > g M A$$